

PLUS Search Results for S/N 09/955,076, Searched May 24, 2002 (Top 50)

4597000	4811078	6117691	5619051	6093607
5266509	5432109	6146904	5698879	6103576
5338954	5731608	4858194	5737261	6121072
5801993	5780894	5198994	5858840	6180977
5859454	5932904	5198996	5950087	6184554
6034892	5942776	5447877	5972753	6188103
6212100	5962884	5483484	5978270	6222227
6212100	6011285	5488579	5989959	6222227
5663084	6018171	5496756	5999444	4355375
4412311	6048738	5515327	6037226	4477884

Most Frequently Occurring Classifications of Patents Returned
From A Search of 09/955,076 on May 24, 2002

Combined Classifications

12 257/316
8 257/295
6 438/3
4 257/315
4 257/324
4 257/326
4 365/145
4 365/185.01
4 365/185.26
4 438/240
4 438/258
4 438/265
4 438/266
3 257/314
3 257/321
3 365/185.14
3 365/185.18
3 365/185.22
3 365/185.23
3 438/257
3 438/264
2 257/256
2 257/318
2 257/322
2 257/411
2 365/185.03
2 365/185.09
2 365/185.11
2 365/185.2
2 365/185.21
2 365/185.25
2 365/185.28
2 365/185.33
2 438/261
2 438/957

- 12 257/316 (5 OR, 7 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/213 FIELD EFFECT DEVICE
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
257/314 ..Variable threshold (e.g., floating gate memory device)
257/315 ...With floating gate electrode
257/316With additional contacted control electrode
- 8 257/295 (6 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/213 FIELD EFFECT DEVICE
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
257/295 . With ferroelectric material layer
- 6 438/3 (3 OR, 3 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/3 HAVING MAGNETIC OR FERROELECTRIC COMPONENT
- 4 257/315 (1 OR, 3 XR)
Class 257 ACTIVE SOLID-STATE DEVICES
257/213 FIELD EFFECT DEVICE
257/288 Having insulated electrode (e.g., MOSFET, MOS diode)
257/314 Variable threshold (e.g., floating gate memory device)
257/315 .With floating gate electrode
- 4 257/324 (0 OR, 4 XR)
Class 257 ACTIVE SOLID-STATE DEVICES
257/213 FIELD EFFECT DEVICE
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
257/314 Variable threshold (e.g., floating gate memory device)
257/324 .Multiple insulator layers (e.g., MNOS structure)
- 4 257/326 (2 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/213 FIELD EFFECT DEVICE
257/288 Having insulated electrode (e.g., MOSFET, MOS diode)
257/314 Variable threshold (e.g., floating gate memory device)
257/324 .Multiple insulator layers (e.g., MNOS structure)
257/326 ..With additional, non-memory control electrode or channel portion (e.g., accessing field effect transistor structure)

- 4 365/145 (2 OR, 2 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/129 SYSTEMS USING PARTICULAR ELEMENT
365/145 .Ferroelectric
- 4 365/185.01 (2 OR, 2 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/185.01 FLOATING GATE
- 4 365/185.26 (0 OR, 4 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/185.01 FLOATING GATE
365/185.18 .Particular biasing
365/185.26 ..Floating electrode (e.g., source, control
gate, drain)
- 4 438/240 (0 OR, 4 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR
ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
- 438/197 ..Having insulated gate (e.g., IGFET, MISFET,
MOSFET, etc.)
- 438/238 ..Including passive device (e.g., resistor,
capacitor, etc.)
- 438/239 ...Capacitor
- 438/240Having high dielectric constant insulator
(e.g., Ta2O5, etc.)
- 4 438/258 (2 OR, 2 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR
ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
- 438/197 ..Having insulated gate (e.g., IGFET, MISFET,
MOSFET, etc.)
- 438/257 ..Having additional gate electrode surrounded
by dielectric (i.e., floating gate)
- 438/258 ..Including additional field effect transistor
(e.g., sense or access transistor, etc.)
- 4 438/265 (1 OR, 3 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR
ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
- 438/197 ..Having insulated gate (e.g., IGFET, MISFET,
MOSFET, etc.)
- 438/257 ..Having additional gate electrode surrounded
by dielectric (i.e., floating gate)
- 438/265 ...Oxidizing sidewall of gate electrode